Yukinori Ono

List of Publications by Year in descending order

36 papers	1,241 citations	471509 17 h-index	454955 30 g-index
37 all docs	37 docs citations	37 times ranked	836 citing authors

#	Article	IF	Citations
1	Nanoampere charge pump by single-electron ratchet using silicon nanowire metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2008, 92, .	3.3	166
2	Manipulation and detection of single electrons for future information processing. Journal of Applied Physics, 2005, 97, 031101.	2.5	112
3	Silicon single-electron devices. Journal of Physics Condensed Matter, 2002, 14, R995-R1033.	1.8	111
4	Current quantization due to single-electron transfer in Si-wire charge-coupled devices. Applied Physics Letters, 2004, 84, 1323-1325.	3.3	94
5	Metalâ''Semiconductor Transition in Single-Walled Carbon Nanotubes Induced by Low-Energy Electron Irradiation. Nano Letters, 2005, 5, 1575-1579.	9.1	87
6	Photoluminescence from a Silicon Quantum Well Formed on Separation by Implanted Oxygen Substrate. Japanese Journal of Applied Physics, 1995, 34, 950-954.	1.5	86
7	Si complementary single-electron inverter with voltage gain. Applied Physics Letters, 2000, 76, 3121-3123.	3.3	84
8	Room-temperature-operating data processing circuit based on single-electron transfer and detection with metal-oxide-semiconductor field-effect transistor technology. Applied Physics Letters, 2006, 88, 183101.	3.3	64
9	Electron pump by a combined single-electron/field-effect- transistor structure. Applied Physics Letters, 2003, 82, 1221-1223.	3.3	59
10	Quantized electron transfer through random multiple tunnel junctions in phosphorus-doped silicon nanowires. Physical Review B, 2007, 76, .	3.2	54
11	Why the long-term charge offset drift in Si single-electron tunneling transistors is much smaller (better) than in metal-based ones: Two-level fluctuator stability. Journal of Applied Physics, 2008, 104, .	2.5	43
12	Charge offset stability in tunable-barrier Si single-electron tunneling devices. Applied Physics Letters, 2007, 90, 033507.	3.3	34
13	Multilevel memory using an electrically formed single-electron box. Applied Physics Letters, 2004, 85, 1277-1279.	3.3	31
14	Mechanism of metal-semiconductor transition in electric properties of single-walled carbon nanotubes induced by low-energy electron irradiation. Journal of Applied Physics, 2007, 101, 034317.	2.5	27
15	Turnstile Operation Using a Silicon Dual-Gate Single-Electron Transistor. Japanese Journal of Applied Physics, 2003, 42, L1109-L1111.	1.5	24
16	Silicon Single-Electron Devices. Nanostructure Science and Technology, 2009, , 125-172.	0.1	23
17	Single-electron and quantum SOI devices. Microelectronic Engineering, 2001, 59, 435-442.	2.4	20
18	Escape dynamics of a few electrons in a single-electron ratchet using silicon nanowire metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2008, 93, .	3.3	20

#	Article	IF	Citations
19	Observation and Circuit Application of Negative Differential Conductance in Silicon Single-Electron Transistors. Japanese Journal of Applied Physics, 2002, 41, 2569-2573.	1.5	18
20	Single-Electron Transistor and Current-Switching Device Fabricated by Vertical Pattern-Dependent Oxidation. Japanese Journal of Applied Physics, 2000, 39, 2325-2328.	1.5	16
21	Single-Electron Device With Si Nanodot Array and Multiple Input Gates. IEEE Nanotechnology Magazine, 2009, 8, 535-541.	2.0	13
22	Single-electron thermal noise. Nanotechnology, 2014, 25, 275201.	2.6	11
23	Fabrication of single-electron transistors and circuits using SOIs. Solid-State Electronics, 2002, 46, 1723-1727.	1.4	9
24	Time-domain charge pumping on silicon-on-insulator MOS devices. Japanese Journal of Applied Physics, 2017, 56, 011303.	1.5	9
25	Development of silicon single-electron devices. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 19, 95-101.	2.7	7
26	Fabrication and single-electron-transfer operation of a triple-dot single-electron transistor. Journal of Applied Physics, 2015, 118, .	2.5	6
27	Silicon nanodot-array device with multiple gates. Materials Science in Semiconductor Processing, 2008, 11, 175-178.	4.0	5
28	Silicon single-charge transfer devices. Journal of Physics and Chemistry of Solids, 2008, 69, 702-707.	4.0	2
29	Effect of Arrangement of Input Gates on Logic Switching Characteristics of Nanodot Array Device. IEICE Transactions on Electronics, 2012, E95.C, 865-870.	0.6	2
30	Silicon Single-Electron Pump and Turnstile: Interplay with Crystalline Imperfections. Materials Research Society Symposia Proceedings, 2005, 864, 671.	0.1	1
31	Silicon Single-Electron Transistors and Single-Electron CCD. Materials Research Society Symposia Proceedings, 2001, 686, 1.	0.1	0
32	Silicon-Based, Tunable-Barrier Single Charge Sources. , 2004, , .		0
33	Si Nanodot Device Fabricated by Thermal Oxidation and their Applications. Key Engineering Materials, 2011, 470, 175-183.	0.4	0
34	Silicon single-electron transfer devices: Ultimate control of electric charge. , 2012, , .		0
35	Detection of single holes generated by impact ionization in silicon. Applied Physics Letters, 2018, 113, 163103.	3.3	0
36	Full Adder Operation Based on Si Nanodot Array Device with Multiple Inputs and Outputs. , 0, , 131-139.		0